Bahram Nabet

List of Publications by Year
in descending order

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		759233	642732
24	672	12	23
papers	citations	h-index	g-index

25	25	25	1154
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Terahertz Polarizers Based on 2D Ti₃C₂T_z MXene: Spin Cast from Aqueous Suspensions. Advanced Photonics Research, 2020, 1, 2000084.	3.6	8
2	Terahertz Polarizers Based on 2D Ti₃C₂T_z MXene: Spin Cast from Aqueous Suspensions. Advanced Photonics Research, 2020, 1, .	3.6	3
3	Mxene Photodetectors: Beyond Gold: Spinâ€Coated Ti₃C₂â€Based MXene Photodetectors (Adv. Mater. 43/2019). Advanced Materials, 2019, 31, 1970307.	21.0	3
4	Beyond Gold: Spinâ€Coated Ti₃C₂â€Based MXene Photodetectors. Advanced Materials, 2019, 31, e1903271.	21.0	114
5	Enhancement of Optoelectronic Properties of Coreâ€“Shell Nanowires. IEEE Nanotechnology Magazine, 2018, 17, 1058-1062.	2.0	3
6	Nanowire Optoelectronics. Nanophotonics, 2015, 4, 491-502.	6.0	33
7	Anomalous Capacitance Enhancement Triggered by Light. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 1-5.	2.9	10
8	An Unconventional Hybrid Variable Capacitor With a 2-D Electron Gas. IEEE Transactions on Electron Devices, 2014, 61, 445-451.	3.0	22
9	High-Speed, High-Sensitivity Optoelectronic Device with Bilayer Electron and Hole Charge Plasma. ACS Photonics, 2014, 1, 560-569.	6.6	11
10	A Planar Switchable Capacitor with Embedded Two-Dimensional Electron System for Higher Integrations in VLSI and RFIC. , 2012, , .		1
11	Polarization anisotropy of individual core/shell GaAs/AlGaAs nanowires by photocurrent spectroscopy. Applied Physics Letters, 2011, 98, .	3.3	25
12	On optical properties of GaAs and GaAs/AlGaAs core-shell periodic nanowire arrays. Journal of Applied Physics, 2011, 109, 064314.	2.5	47
13	Low-temperature grown GaAs heterojunction metal-semiconductor-metal photodetectors improve speed and efficiency. Applied Physics Letters, 2011, 99, .	3.3	14
14	Picosecond response times in GaAs/AlGaAs core/shell nanowire-based photodetectors. Applied Physics Letters, 2011, 98, .	3.3	102
15	On direct-writing methods for electrically contacting GaAs and Ge nanowire devices. Applied Physics Letters, 2010, 96, 223107.	3.3	23
16	Single-Layer InAs Quantum Dots for High-Performance Planar Photodetectors Near 1.3 $muhbox{m}$. IEEE Transactions on Electron Devices, 2010, 57, 1237-1242.	3.0	1
17	Integrated plasmonic lens photodetector. Applied Physics Letters, 2009, 94, .	3.3	76
18	Time Response of Two-Dimensional Gas-Based Vertical Field Metalâ€“Semiconductorâ€“Metal Photodetectors. IEEE Transactions on Electron Devices, 2008, 55, 1762-1770.	3.0	15

#	Article	IF	Citations
19	Physical modeling of a novel barrier-enhanced quantum-well photodetector device for optical receivers. Microwave and Optical Technology Letters, 2004, 40, 224-227.	1.4	3
20	Closed-form electric-field profile model for AlGaAs/GaAs heterostructures. Journal of Applied Physics, 2002, 92, 218-222.	2.5	1
21	Effects of electron confinement on thermionic emission current in a modulation doped heterostructure. Journal of Applied Physics, 1999, 85, 2663-2666.	2.5	103
22	Role of intermediate temperature molecular beam epitaxy grown GaAs defects in tunneling and diffusion. Journal of Applied Physics, 1998, 84, 2697-2704.	2.5	3
23	Simple analytical model of bias dependence of the photocurrent of metalâ€“semiconductorâ€“metal photodetectors. Applied Optics, 1996, 35, 15.	2.1	35
24	Intermediate temperature molecular beamâ€epitaxy growth for design of largeâ€area metalâ€semiconductorâ€metal photodetectors. Applied Physics Letters, 1994, 64, 3151-3153.	3.3	16